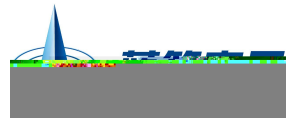
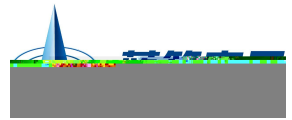


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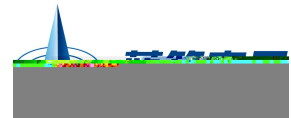


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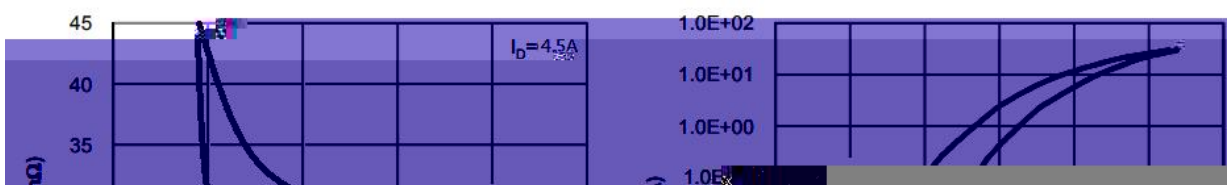
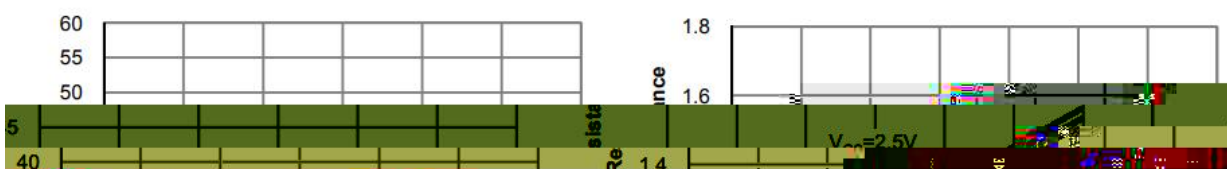
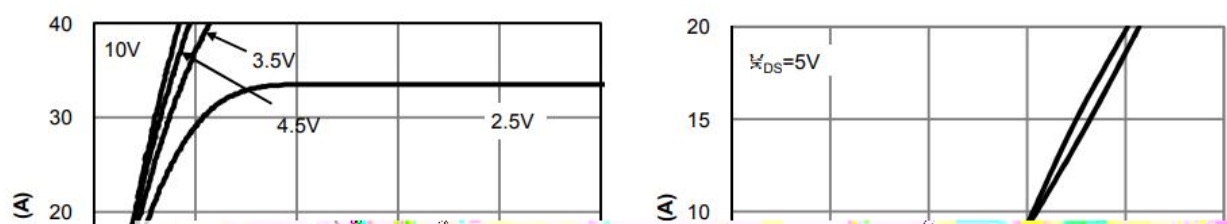
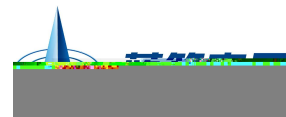
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SOT23-3 N MOS
- CHANNEL MOSFET in a SOT23-3 Plastic Package.



Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DSS}	20	V
Gate-Source Voltage		V_{GSS}	± 10	V
Drain Current – Continuous		I_D	4.5	A
Pulsed Drain Current		I_{DM}	12	A
Power Dissipation		P_D	1.4	W
Storage Temperature Range		T_{stg}	-55~150	$^{\circ}C$
Maximum Junction-to-Ambient	t 10s	R_{JA}	90	$^{\circ}C/W$
Maximum Junction-to-Ambient				

Parameter	Symbol	Test Conditions	Unit
Total Gate Charge	Qg(10V)	$V_{GS}=10V, V_{DS}=10V$ $I_D=4.5A$	nC
Total Gate Charge	Qg(4.5V)		
Gate Source Charge	Qgs		
Gate Drain Charge	Qgd		
Turn-On Delay Time	$t_{d(on)}$	$V_{GS}=10V, V_{DS}=10V$ $R_{GEN}=3, R_L=1.7$	ns
Turn-On Rise Time	t_r		
Turn-Off Delay Time	$t_{d(off)}$		
Turn-Off Fall Time			
			20
			6



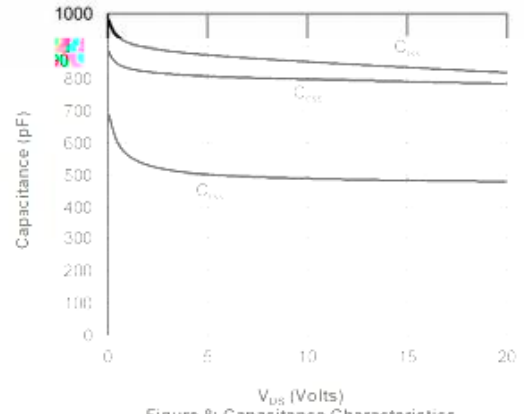
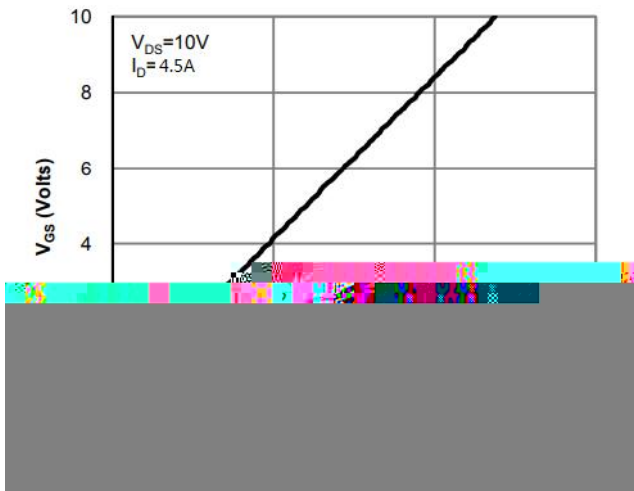
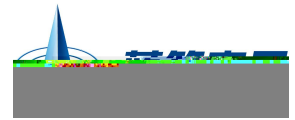
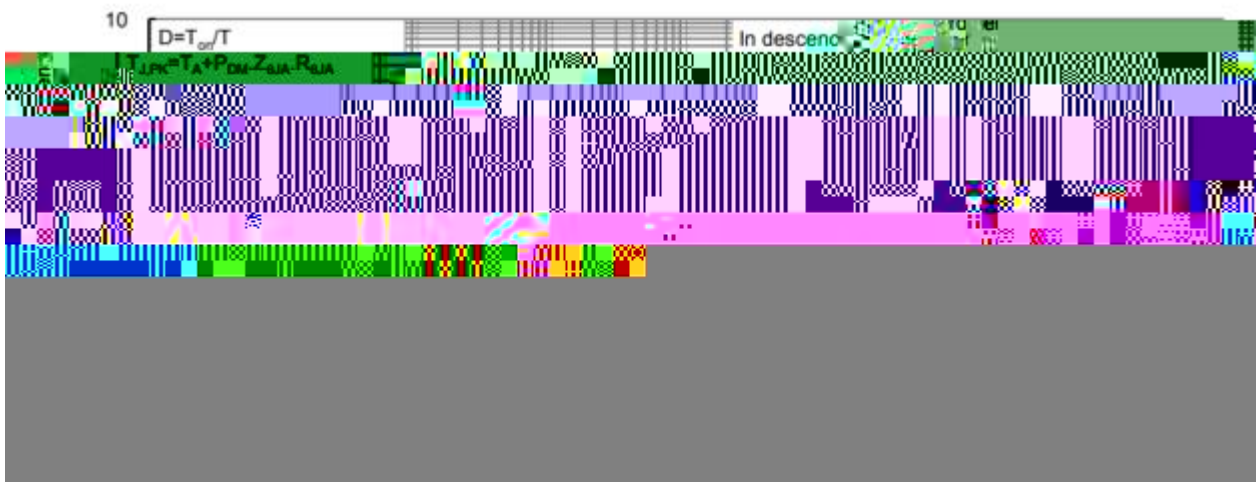
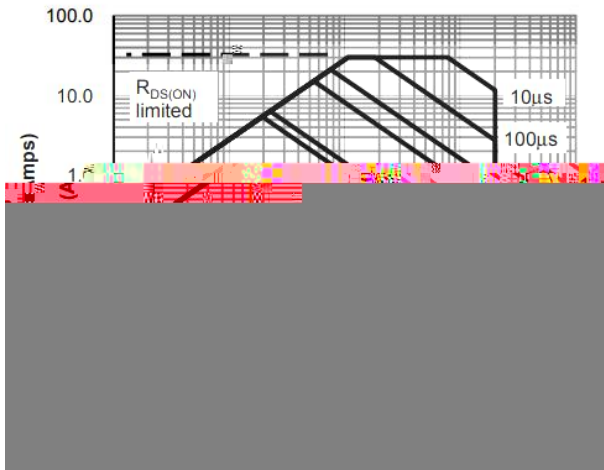
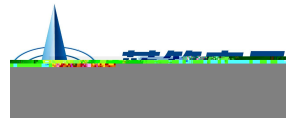
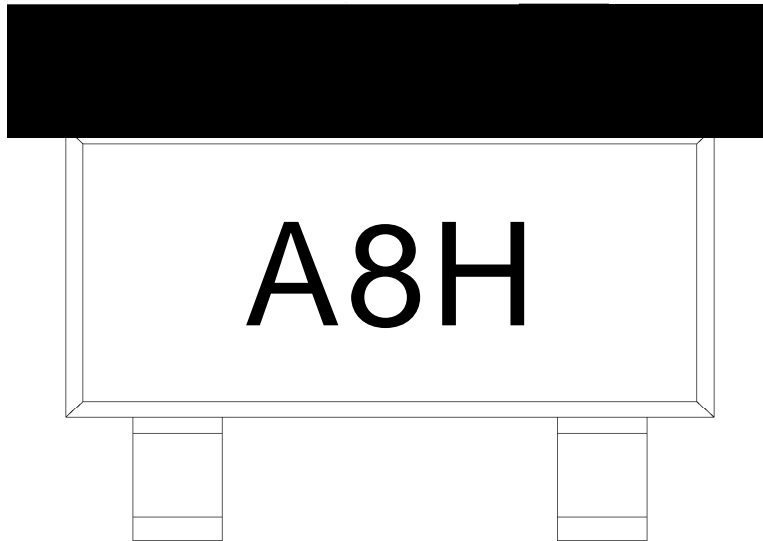
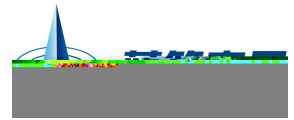


Figure 8: Capacitance Characteristics



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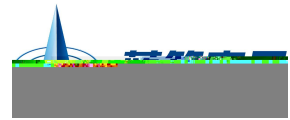
A8:

H:

Note:

A8 Product Type Code

H: Company Code.



Temperature Profile for IR Reflow Soldering(Pb-Free)

Note:

1

150